

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L²-π-MOSV)

2SK3205

HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS

SWITCHING REGULATOR APPLICATIONS, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

- 4 V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.36 \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 4.5 S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu A$ (Max.) ($V_{DS} = 150 V$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0 V$ ($V_{DS} = 10 V, I_D = 1 mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	150	V
Drain-Gate Voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	150	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	5	A
	Pulse	I_{DP}	20	
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	20	W
Single Pulse Avalanche Energy*		E_{AS}	71	mJ
Avalanche Current		I_{AR}	5	A
Repetitive Avalanche Energy**		E_{AR}	2	mJ
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	6.25	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	125	$^\circ C / W$

Note ;

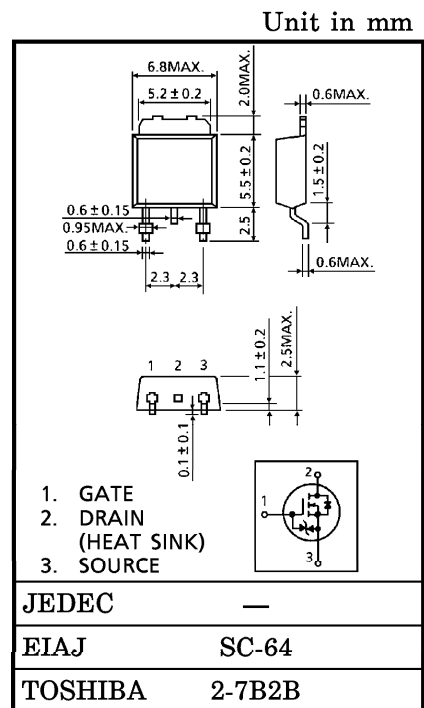
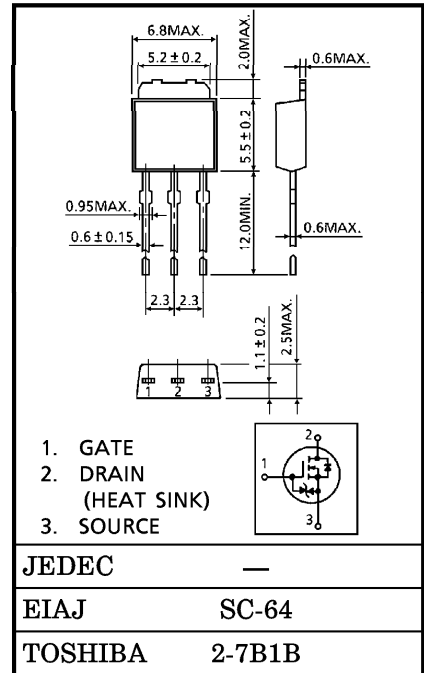
* $V_{DD} = 50 V, T_{ch} = 25^\circ C$ (initial), $L = 4.2 mH,$

$I_{AR} = 5 A, R_G = 25 \Omega$

** Repetitive rating ; Pulse Width Limited by Max.

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

INDUSTRIAL APPLICATIONS
Unit in mm



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	150	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	0.8	—	2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 4\text{ V}, I_D = 2.5\text{ A}$	—	0.54	0.75	Ω
		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$	—	0.36	0.5	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 2.5\text{ A}$	2.0	4.5	—	S
Input Capacitance		C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	—	330	—	pF
Reverse Transfer Capacitance		C_{rss}		—	50	—	
Output Capacitance		C_{oss}		—	145	—	
Switching Time	Rise Time	t_r	<p>$I_D = 2.5\text{ A}$ $V_{GS} = 10\text{ V}, 0\text{ V}$ 4.7Ω $R_L = 40\Omega$ $V_{DD} \approx 100\text{ V}$ V_{OUT}</p> <p>$V_{IN} : t_r, t_f < 5\text{ ns},$ $Duty \leq 1\%, t_w = 10\ \mu\text{s}$</p>	—	10	—	ns
	Turn-on Time	t_{on}		—	15	—	
	Fall Time	t_f		—	10	—	
	Turn-off Time	t_{off}		—	60	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \approx 120\text{ V}, V_{GS} = 10\text{ V},$ $I_D = 5\text{ A}$	—	12	—	nC
Gate-Source Charge		Q_{gs}		—	8	—	
Gate-Drain (“Miller”) Charge		Q_{gd}		—	4	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	20	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}$	—	110	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	0.47	—	nC